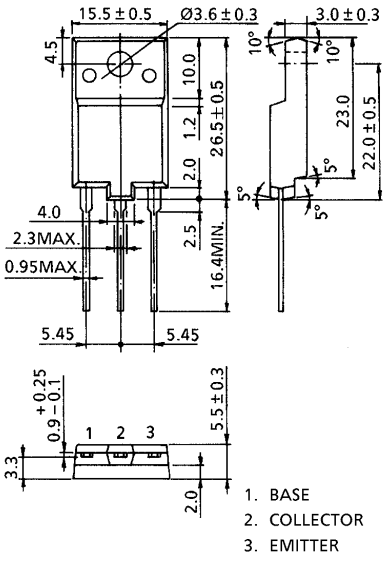
TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SD2500

HORIZONTAL DEFLECTION OUTPUT FOR COLOR TV

Unit in mm

- High Voltage : V_{CBO} = 1500 V
- Low Saturation Voltage : $V_{CE\ (sat)}$ = 3 V (Max.)
- High Speed : t_f = 0.35 μs (Typ.)
- Collector Metal (Fin) is Fully Covered with Mold Resin.



JEDEC	—
EIAJ	—
TOSHIBA	2-16E3A

Weight : 5.5 g (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	1500	V
Collector-Emitter Voltage		V_{CEO}	600	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	10	A
	Pulse	I_{CP}	20	
Base Current		I_B	5	A
Collector Power Dissipation (Tc = 25°C)		P_C	50	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB} = 1500 V, I_E = 0	—	—	1	mA
Emitter Cut-off Current		I_{EBO}	V_{EB} = 5 V, I_C = 0	—	—	10	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)\ CEO}$	I_C = 10 mA, I_B = 0	600	—	—	V
DC Current Gain		h_{FE} (1)	V_{CE} = 5 V, I_C = 1 A	10	—	30	
		h_{FE} (2)	V_{CE} = 5 V, I_C = 6 A	4	—	8	
Collector-Emitter Saturation Voltage		$V_{CE\ (sat)}$	I_C = 6 A, I_B = 1.5 A	—	—	3	V
Base-Emitter Saturation Voltage		$V_{BE\ (sat)}$	I_C = 6 A, I_B = 1.5 A	—	1.0	1.4	V
Transition Frequency		f_T	V_{CE} = 10 V, I_C = 0.1 A	—	1.7	—	MHz
Collector Output Capacitance		C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz	—	135	—	pF
Switching Time	Storage Time	t_{stg}	I_{CP} = 6 A, I_{B1} (end) = 1.5 A	—	—	11	μs
	Fall Time	t_f	f_H = 15.75 kHz	—	0.35	0.7	

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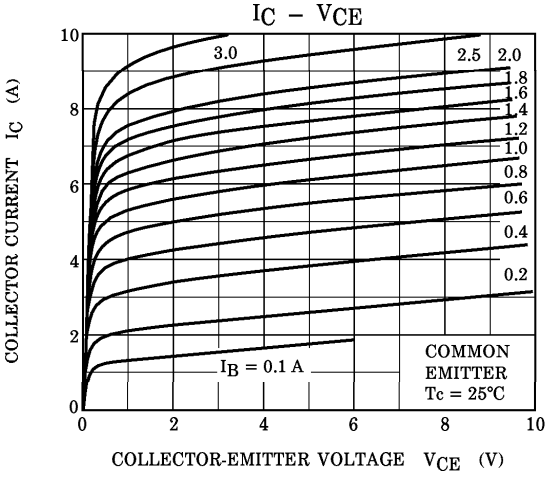
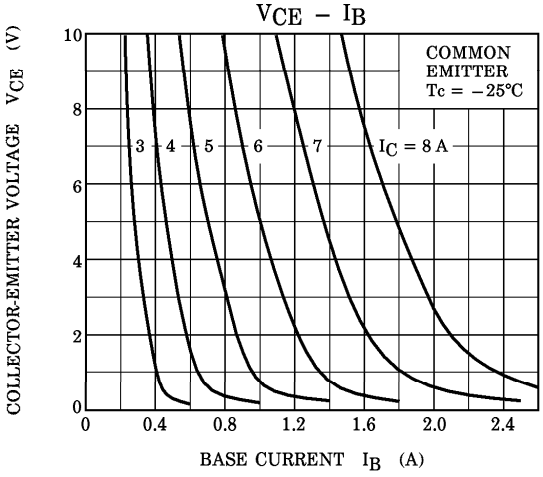
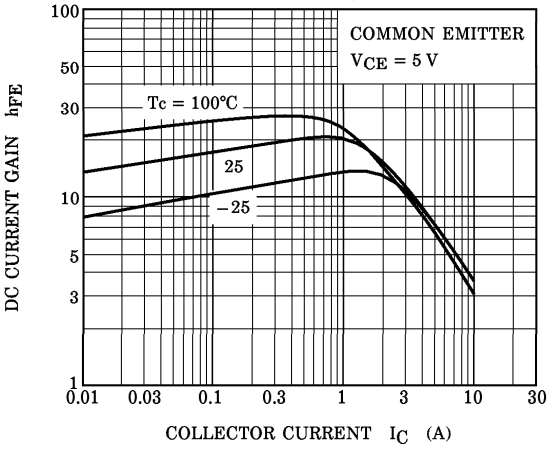
I_C – V_{CE}



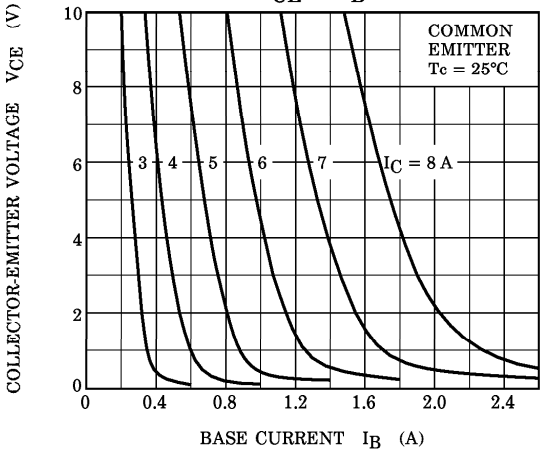
V_{CE} – I_B



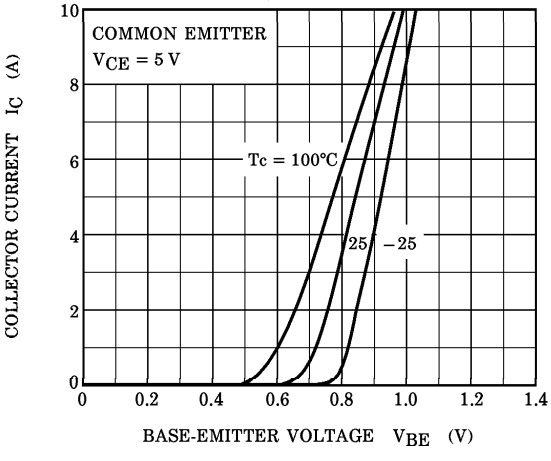
h_{FE} – I_C



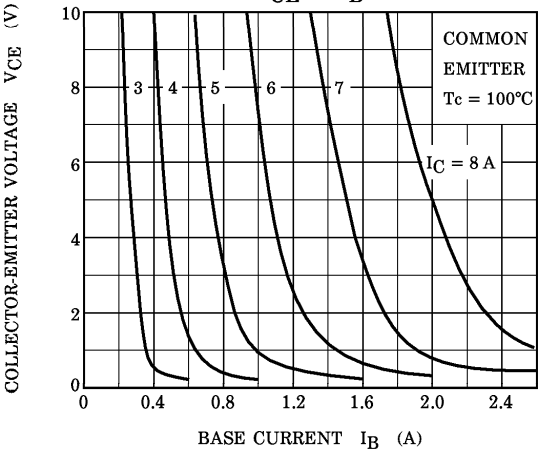
V_{CE} – I_B



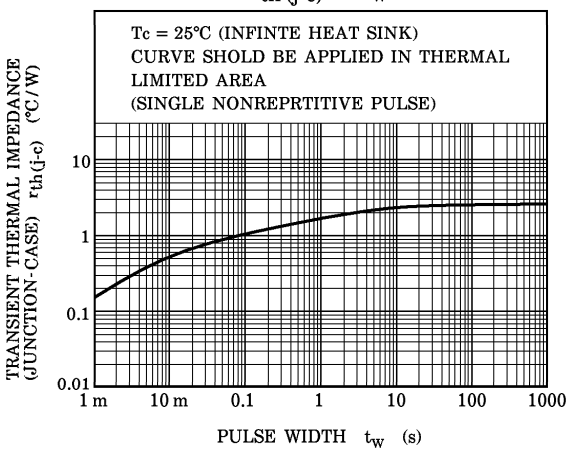
I_C – V_{BE}



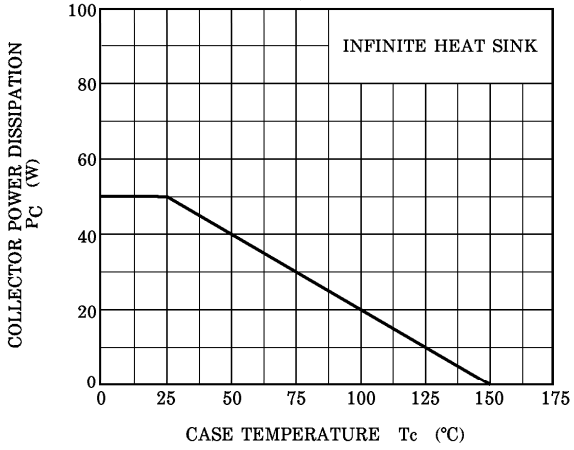
V_{CE} – I_B



$r_{th\,(j\text{-}c)}$ – t_w



P_C – Tc



SAFE OPERATING AREA